

SPTECH Silicon PNP Power Transistor**2SB940****DESCRIPTION**

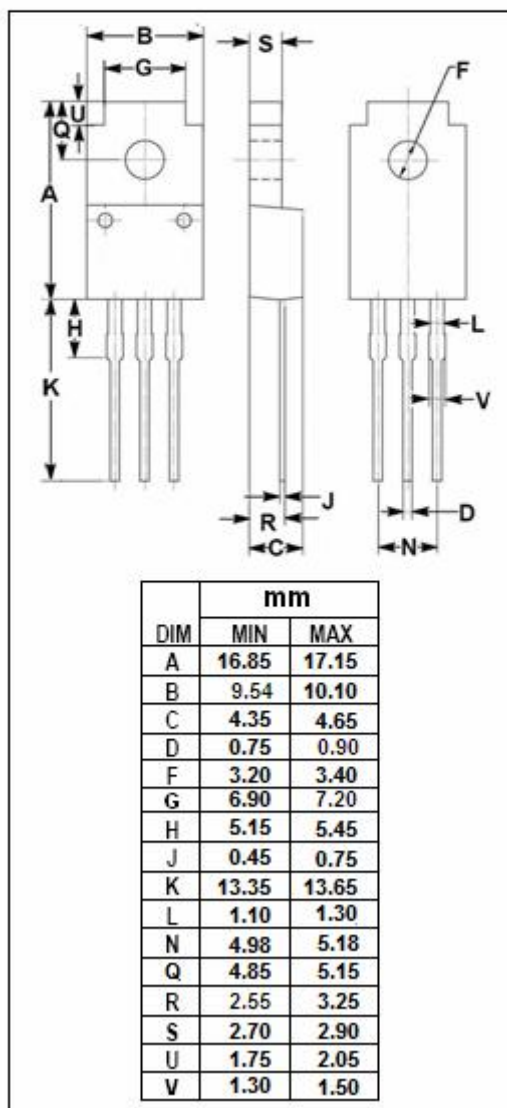
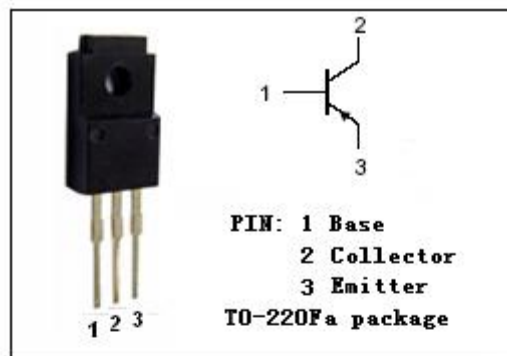
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min.})$
- High Collector Power Dissipation
- Complement to Type 2SD1264

APPLICATIONS

- Designed for power amplifications and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SB940****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA; I _B = 0	-150			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μ A; I _E = 0	-200			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -0.5mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.4A; V _{CE} = -10V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -200V; I _E = 0			-50	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-50	μ A
h _{FE-1}	DC Current Gain	I _C = -150mA; V _{CE} = -10V	60		240	
h _{FE-2}	DC Current Gain	I _C = -0.4A; V _{CE} = -10V	50			
f _T	Current-Gain—Bandwidth Product	I _C =-0.5A; V _{CE} = -10V; f _{test} =10MHz		30		MHz

◆ **h_{FE-1} Classifications**

Q	P
60-140	100-240